PTO/SB/08B (04-03)
Approved for use through 04/30/2003. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	~~Not Known Yet~~ 10/683901
Filing Date	10/10/2003
First Named Inventor	Chung-Hu Ke
Art Unit	~~Not Known Yet~~ 2813
Examiner Name	~~Not Known Yet~~ SCHILLINGER
Attorney Docket Number	N1085-00163

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	A	STEEGEN ET AL., "Silicide Induced pattern Density And Orientation Dependent Transconductance in MOS Transistors," 1999 IEEE, IEDM 99, Pages 497 - 500	
	B	BUFLER ET AL., "Hole And Electron Transport In Strained Si: Orthorhombic Versus Biaxial Tensile Strain," Applied Physics Letters, Volume 81, Number 1, 1 July 2002, Pages 82 - 84	
	C	DOMBROWSKI ET AL., "Detemination Of Stress In Shallow Trench Isolation For Deep Submicron MOS Devices By UV Raman Spectroscopy," 1999 IEEE, IEDM 99, Pages 357 - 360	
	D	SCOTT ET AL., "NMOS Drive Current Reduction Caused By Transistor Layout And Trench Isolation Induced Stress," 1999 IEEE, IEDM 99, Pages 827 - 830	
	E	IBM's Strained Silicon Breakthrough Image, Pages 1 - 2, cited at http://www.research.ibm.com/resources/press/strainedsilicon/ dated 4/8/2003	

Examiner Signature		Date Considered	4/28/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: **Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

OIPE JC116 MAR 0 8 2004 PATENT & TRADEMARK OFFICE

PTO/SB/08B (04-03)
Approved for use through 04/30/2003. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	10/683,901
Filing Date	10/10/2003
First Named Inventor	Chung-Hu Ke
Art Unit	~~Not Known Yet~~ 2813
Examiner Name	~~Not Known Yet~~ Schillinger
Attorney Docket Number	N1085-00163

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	A	C. K. MAITI ET AL., "Applications of Silicon-Germanium Heterostructure Devices", Institute of Physics Publishing, Chapter 2, pp. 32-72, 2001	
	B	YUKIHIRO KUMAGAI ET AL., "Evaluation of change in drain current due to strain in 0.13-um-node MOSFETs", Extended Abstracts of the 2002 International Conference on	
		Solid State Devices and Materials, pp. 14-15, 2002	

Examiner Signature		Date Considered	4/28/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: **Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.